

FEATURES

- Available as "HR" (high reliability) screened per MIL-PRF-19500, JANTX level. Add "HR" suffix to base part number.
- Available as non-RoHS (Sn/Pb plating), standard, and as RoHS by adding "-PBF" suffix.

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak repetitive forward and reverse blocking voltage⁽¹⁾ (T _j = 25 to +125°C, gate open)	V _{RRM} , V _{DRM}	25 50 100 200 300 400 500 600 700 800	Volts
MCR64-1			
MCR64-2			
MCR64-3			
MCR64-4			
MCR64-5			
MCR64-6			
MCR64-7			
MCR64-8			
MCR64-9			
MCR64-10			
Non-repetitive peak reverse blocking voltage (t ≤ 5ms) ⁽¹⁾	V _{RSM}	35 75 150 300 400 500 600 700 800 900	Volts
MCR64-1			
MCR64-2			
MCR64-3			
MCR64-4			
MCR64-5			
MCR64-6			
MCR64-7			
MCR64-8			
MCR64-9			
MCR64-10			
Forward current RMS	I _{T(RMS)}	55	Amps
Peak surge current (one cycle, 60Hz, T _c = -40 to +125°C)	I _{TSM}	550	Amps
Circuit fusing considerations (t = 8.3ms)	I ² t	1255	A ² s
Peak gate power	P _{GM}	20	Watts
Average gate power (Pulse width ≤ 2μs)	P _{G(AV)}	0.5	Watts
Peak forward gate current	I _{GM}	2	Amps
Forward peak gate voltage	V _{GFM}	10	Volts
Reverse peak gate voltage	V _{GRM}		
Operating junction temperature range	T _j	-40 to +125	°C
Storage temperature range	T _{stg}	-40 to +150	°C
Mounting torque		30	In. lb.

Note 1: V_{DRM} and V_{RRM} for all types can be applied on a continuous basis without incurring damage. Ratings apply for zero or negative gate voltage. Devices shall not have a positive bias applied to the gate concurrently with a negative potential on the anode.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Maximum	Unit
Thermal resistance, junction to case Pressfit	$R_{\theta JC}$	1	°C/W

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

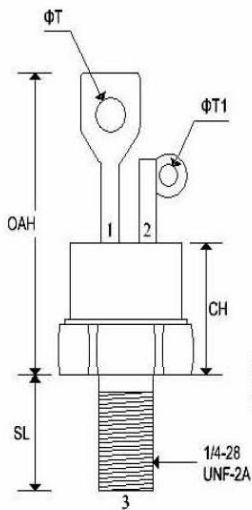
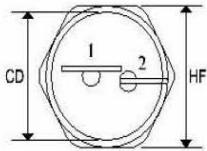
Characteristic	Symbol	Min.	Max.	Unit
Peak forward or reverse blocking current ($V_{AK} = \text{Rated } V_{DRM} \text{ or } V_{RRM}, \text{ gate open}$) $T_C = 25^\circ\text{C}$ $T_C = 125^\circ\text{C}$	I_{DRM}, I_{RRM}	-	10 2	μA mA
Forward "on" voltage ($I_{TM} = 175\text{A peak}$)	V_{TM}	-	2	Volts
Gate trigger current (continuous dc) ($V_D = 12\text{V}, R_L = 50\Omega$) $T_C = 25^\circ\text{C}$ $T_C = -40^\circ\text{C}$	I_{GT}	-	40 75	mA
Gate trigger voltage (continuous dc) ($V_D = 12\text{V}, R_L = 50\Omega$) $T_C = 25^\circ\text{C}$ $T_C = -40^\circ\text{C}$ ($V_D = \text{Rated } V_{DRM}, R_L = 1000\Omega, T_J = 125^\circ\text{C}$)	V_{GT}	- - 0.2	3 3.5 -	Volts
Holding current ($V_D = 12\text{V}, R_L = 50\Omega, \text{ gate open}$)	I_H	-	60	mA
Forward voltage application rate ($V_D = \text{rated } V_{DRM}, T_J = 125^\circ\text{C}$)	dv/dt	50	-	V/ μs

MCR64 SERIES

SILICON CONTROLLED RECTIFIER

MECHANICAL CHARACTERISTICS

Case	TO-48
Marking	Body painted, alpha-numeric
Polarity	Cathode is stud



Pin 1: Cathode
Pin 2: Gate
Pin 3: Anode

1/4-28
UNF-2A

	TO-48			
	Inches		Millimeters	
	Min	Max	Min	Max
CD	-	0.543	-	13.793
CH	-	0.560	-	13.970
HF	0.544	0.563	13.817	14.301
OAH	-	1.193	-	30.303
SL	0.422	0.453	10.718	11.507
ΦT	0.125	0.165	3.175	4.191
ΦT ₁	0.060	0.075	1.524	1.905

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FIGURE 1 – AVERAGE CURRENT DERATING

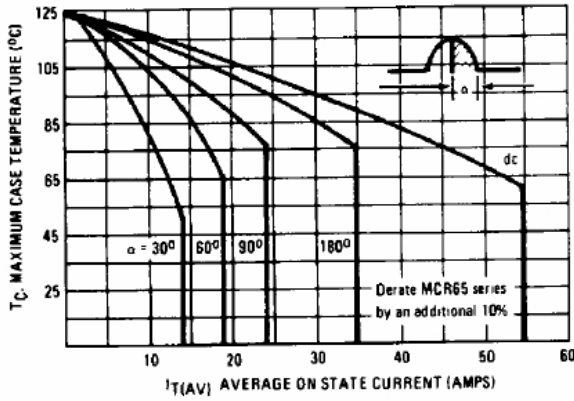


FIGURE 2 – POWER DISSIPATION

